

PNP BD132

SILICON PLANAR EPITAXIAL POWER TRANSISTORS

The BD132 are PNP transistors mounted in Jedec TO-126 plastic package.
 Medium power applications.
 PNP complements are BD131
 Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

| Symbol | Ratings | Value | Unit |
|------------|-----------------------------------|-------------------------------|-------------|
| $-V_{CEO}$ | Collector-Emitter Voltage | 45 | V |
| $-V_{CBO}$ | Collector-Base Voltage | 45 | V |
| $-V_{EBO}$ | Emitter-Base Voltage | 4 | V |
| I_C | Collector Current | $-I_C$ | 3 |
| | | $-I_{CM}$ | 6 |
| I_B | Base current (peak value) | $-I_{BM}$ | 0.5 |
| | Reverse base current (peak value) | $-I_{BM}$ | 0.5 |
| P_T | Total power Dissipation | @ $T_{mb} = 60^\circ\text{C}$ | 15 |
| T_J | Junction Temperature | | 150 |
| T_{Stg} | Storage Temperature | | -65 to +150 |

THERMAL CHARACTERISTICS

| Symbol | Ratings | Value | Unit |
|--------------|---|-------|------|
| R_{thJ-mb} | Thermal Resistance, Junction to mounting base | 6 | K/W |

ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

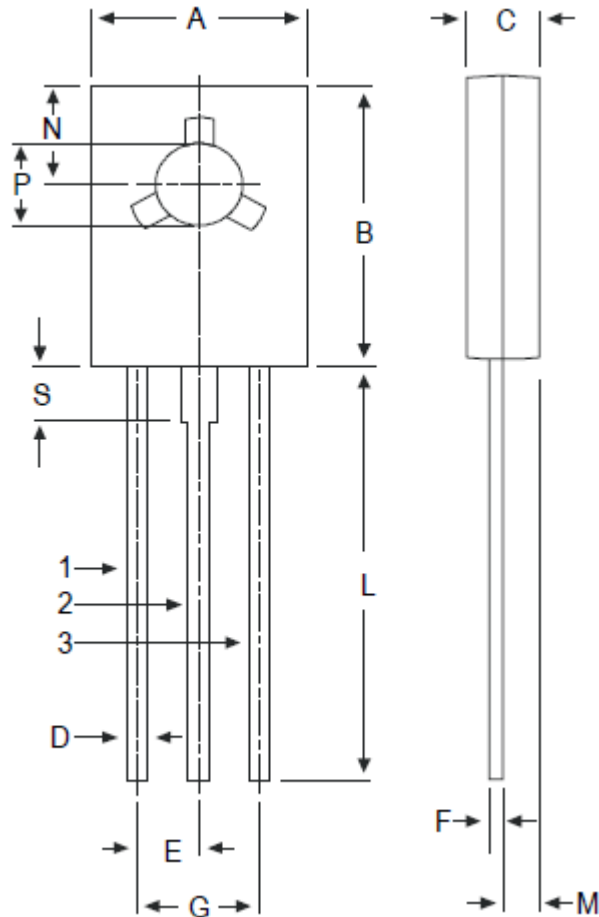
| Symbol | Ratings | Test Condition(s) | Min | Typ | Max | Unit |
|----------------|--------------------------------------|---|-----|-----|-----|---------------|
| $-I_{CBO}$ | Collector cut-off current | $I_E=0, -V_{CB}=40\text{ V}$ | - | - | 5 | μA |
| | | $I_E=0, -V_{CB}=40\text{ V}, T_J=150^\circ\text{C}$ | - | - | 500 | |
| $-I_{EBO}$ | Emitter cut-off current | $I_C=0, -V_{EB}=3\text{ V}$ | - | - | 5 | μA |
| $-V_{CE(SAT)}$ | Collector-Emitter saturation Voltage | $-I_C=0.5\text{ A}, -I_B=50\text{ mA}$ | - | - | 0.3 | V |
| | | $-I_C=2.0\text{ A}, -I_B=200\text{ mA}$ | - | - | 1.2 | |
| $-V_{BE(SAT)}$ | Base-Emitter saturation Voltage | $-I_C=0.5\text{ A}, -I_B=50\text{ mA}$ | - | - | 0.7 | V |
| | | $-I_C=2.0\text{ A}, -I_B=200\text{ mA}$ | - | - | 1,5 | |
| h_{FE} | DC Current Gain | $-V_{CE}=12\text{ V}, -I_C=500\text{ mA}$ | 40 | - | - | |
| | | $-V_{CE}=1\text{ V}, -I_C=2\text{ A}$ | 20 | - | - | |

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MECHANICAL DATA CASE TO-126

| | DIMENSIONS | |
|---|------------|------|
| | min | max |
| A | 7.4 | 7.8 |
| B | 10.5 | 10.8 |
| C | 2.4 | 2.7 |
| D | 0.7 | 0.9 |
| E | 2.25 typ. | |
| F | 0.49 | 0.75 |
| G | 4.4 typ. | |
| L | 15.7 typ. | |
| M | 1.27 typ. | |
| N | 3.75 typ. | |
| P | 3.0 | 3.2 |
| S | 2.54 typ. | |

| | |
|---------|-----------|
| Pin 1 : | Emitter |
| Pin 2 : | Collector |
| Pin 3 : | Base |



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